

In the Claims:

Claim 8 (amended). The method according to claim 7, which further comprises choosing the magnitude of the doping of the further buffer layer such that, in an operating state in which the semiconductor component effects blocking in the direction from the drain contact toward the source contact, at least in an envisaged range of applied electrical voltages, a space charge zone present in the first base region is formed in a manner extending at least as far as the further buffer layer.

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